PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiromi SAITOH

Group Art Unit: 2871

Application No.: 10/608,475

Examiner:

M. T. T. Ton

Filed: June 30, 2003

Docket No.: 104455.01

For:

ELECTRO-OPTICAL PANEL, ELECTRO-OPTICAL PANEL MODULE, AND

PROJECTION DISPLAY DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- X This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- \bowtie English-language Abstracts of the non-English language references are attached hereto. See References 1-3 and 5-11.
- \boxtimes A computer-generated English translation of the following Japanese Patent Publication has been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and is attached, but has not been reviewed for accuracy. See References 1, 4, 5, 6, 7, 8, 10 and 11.
- X The references are cited by or submitted to the Office in parent application No. 09/455,447, filed December 6, 1999, which is relied upon for an earlier filing date under 35 U.S.C. §120. Thus, copies of these references are not attached. 37 CFR §1.98(d).

Respectfully submitted.

James A_Oliff

Registration No. 27,075

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JAO:GWT/gwt

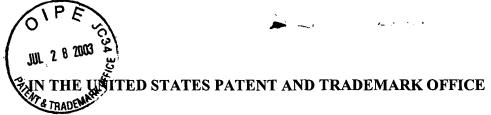
Date: July 28, 2003

OLIFF & BERRIDGE, PLC P.O. Box 19928 Alexandria, Virginia 22320 Telephone: (703) 836-6400

DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461 Sheet 1 of 1

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Form PTO-144 (REV. 8-83)	9 TE	US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY D 104455.	OOCKET NO. 01		PLICATION N 508,475	NO.
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<u>.</u>				FILING June 30,		GR0 287		
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EXAMINER INITIAL		DOCUMENT NUMBER		DATE	NAM	ИЕ	CLASS	SUB CLASS
		FOREIC	GN PA	ATENT DO	OCUMENTS T			
		DOCUMENT NUMBER		DATE	COUNT	ГКҮ	CLASS	SUB CLASS
	1	JP 11-149254A w/Abstract & Translation	06/	1999	Japan			
	2	JP 63-264720A w/Abstract	11/	1998	Japan			
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	4	JP 02-095379U w/Translation	07/	1990	Japan			
	5	JP 05-034655A w/Abstract & Translation	02/1	1993	Japan			
	6	JP 10-123964A w/Abstract & Partial Translation	05/1	1998	Japan			
	7	JP 11-084350A w/Abstract & Translation	03/1	1999	Japan			
	8	JP 06-258637A w/Abstract & Translation	09/1	1994	Japan			
	9	JP 01-302386A w/Abstract	12/1	1989	Japan			_
	10	JP 11-052325A w/Abstract & Translation	02/1	1999	Japan			
	11	JP 10-232629A w/Abstract & Translation	09/1	1998	Japan			
	12	JP 14-387949A	11/2	2002	Japan			
		OTHER DOCUMENTS (Inc	cludin	g Author,	Title, Date, Pertinent Pag	ges, etc.)		
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EXAMINER						DATE CONSID	ERED	
		citation considered, whether or not citation and not considered. Include conv. o					hrough citation	on if not in

Date: July 28, 2003



In re the Application of: FUKUDA, Tetsuo, et al.

Group Art Unit: Not yet assigned

Serial No.: 10/607,013

Examiner: Not yet assigned

Filed: June 27, 2003

*P3374-0698-030766

For:

SEMICONDUCTOR SUBSTRATE AND METHOD FOR FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

July 28, 2003

Sir:

The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached Form PTO-1449. One copy of each of these documents is attached.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the issuance of a first official action on the merits or expiration of the three month period following the filing date or the entry of the national stage of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.

The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this

🔭 🎢 statement.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP

Donald W. Hanson Attorney for Applicants Reg. No. 27,133

DWH/nrp/plb Atty. Docket No. **030766** Suite 1000 1725 K Street, N.W. Washington, D.C. 20006 (202) 659-2930

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PATENT TRADEMARK OFFICE

Enclosures: PTO-1449 (3) and references (23)

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INFORMATION DISCLOSURE CITATION PTO-1449

RADEMAN Atty. Docket No. 030766	Serial No.	10/607,013	
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Applicant(s): FUKUDA, Tetsuo, et al.

Filing Date: June 27, 2003 Group Art Unit:

U.S. PATENT DOCUMENTS

Examiner Initial	·	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA						
	AB						

FOREIGN PATENT DOCUMENTS

Document No.		Date	Country	Translation (Yes or No)	
	AC	Hei 09-246505 (A)	9-1997	Japan	
	AD				

OTHER DOCUMENTS

	AE	T. Tsuchiya, Prospect of SOI devices, OYO BUTURI, Vol. 66, No. 11, pp.1191-1198, (1997)
	AF	Y.Yamaguchi et al., IEEE Trans. Electron Devices, <u>40</u> , p.179, (1993).
	AG	G. Abstreiter et al., Phys. Rev. lett., <u>54</u> , p.2441, (1985).
	AH	D.K. Nayak et al., Appl. Phys. Lett., <u>70</u> , p.2853, (1993).
	AI	K.K. Linder et al., Appl. Phys. Lett., <u>70</u> , p.3224, (1997).
	AJ	E. A. Fitzgerald et al., Appl. Phys. Lett., <u>59</u> , p.811, (1991).
	AK	A. R. Powell et al., Appl. Phys. Lett., 64, p.1856, (1994).
	AL	Y. Ishikawa et al., Appl. Phys. Lett., <u>75</u> , p.983 (1999).
Examiner		Date Considered

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)

FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)

OTHER DOCUMENTS

	AM	T. Mizuno et al., IEEE Electron Devices Lett., EDL-21, p.230, (2000).
	AN	T. Mizuno et al., Tech. Dig. Int. Electron Devices Meet., Washington, (1999), p. 934.
	AO	S. J. Burden, Semiconductor Fabtech, Mar., 2001, 13 th Ed., p.297.
	AP	M. A. Palmer et al., Phy. Rev. B, <u>56</u> , p. 9431, (1997).
	AQ	W.S. Capinski et al., Appl. Phys. Lett. <u>71</u> , p.2109, (1997).
	AR	T. Ruf et al., Solid State Commun., <u>115</u> , p.243, (2000).
	AS	G. Ottaviani et al., Phys. Rev. <u>B12</u> , p.3318 (1975).
	AT	H-J. Mussig et al., Proc. 3 rd Int'l Symp. on Advanced Sci. and Tech. of Si Mat., The Jpn Soc. Prom. Sci., (2000), p.374.
Examiner	· <u>-</u>	Date Considered



INFORMATION	Atty. Docket No. 030766	Serial No. 10/607,013
DISCLOSURE CITATION	Applicant(s): FUKUDA, Tets	suo, et al.
PTO-1449	Filing Date: June 27, 2003	Group Art Unit:

			U.S. PAT	ENT DOCUME			
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			OTH	ED DOCUMENT	'C		
	<u> </u>		OTHE	ER DOCUMENT	<u> </u>		
	AU	T. Sato et al., F	hys. Rev. E	3 <u>,4,</u> p.1950, (1971).		
	AV S. Nakashima, et al., J. Electrochem. Soc. <u>143</u> , p.244, (1996).						
	AW	S. Nakashima	et al., Electi	on, Lett. <u>26</u> , p.16	47, (1990).		
	AX	Jaccodine et al	, J. Appl. P	hys. <u>37</u> , p.2429, (1966).		
	AY	G. Lucovsky e	t al., The Pl et al., Plen	nysics and Chemis um Press, NY, (19	stry of SiO ₂ a 988), p.139.	and the SiO	2 Interface, edited
	AZ	H.J. Herzog, e	t al., J. Elec	trochem. Soc.,133	<u>l</u> , p.2969, (19	984).	
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